

Power Transistor (120V, 1.5A)

2SC4132 / 2SD1857 / 2SD2343

●Features

- 1) High breakdown voltage. ($BV_{CEO} = 120V$)
- 2) Low collector output capacitance.
(Typ. 20pF at $V_{CB} = 10V$)
- 3) High transition frequency. ($f_T = 80MHz$)
- 4) Complements the 2SB1236.

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	2	A
	I_{CP}	3	A
Collector power dissipation	P_C	0.5	W
		2	
		1	W ($T_c = 25^\circ C$)
		1.5	
Junction temperature	T_J	5	$^\circ C$
Storage temperature	T_{stg}	-55~+150	$^\circ C$

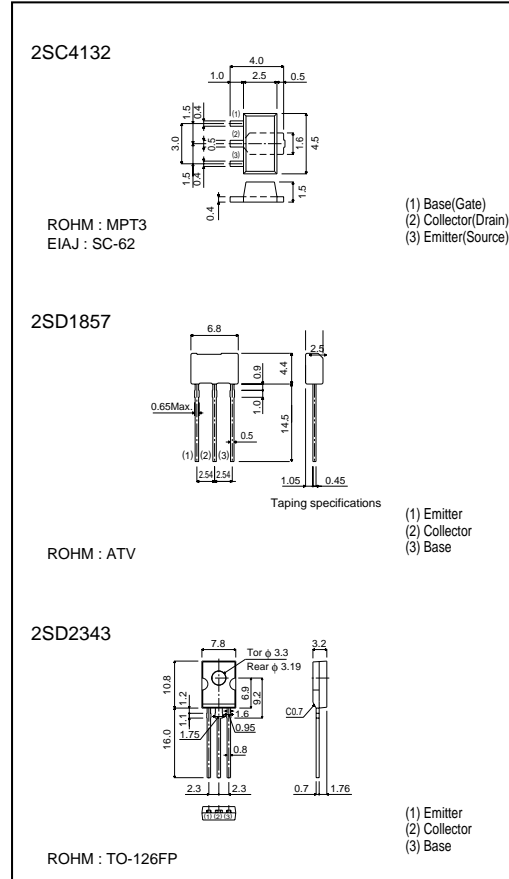
*1 Single pulse $P_w = 10ms$
 *2 When mounted on a $40 \times 40 \times 0.7mm$ ceramic board.

●Packaging specifications and h_{FE}

Type	2SC4132	2SD1857	2SD2343
Package	MPT3	ATV	TO-126FP
h_{FE}	PQR	PQR	PQ
Marking	CB*	-	-
Code	T100	TV2	-
Basic ordering unit (pieces)	1000	2500	1000

* Denotes h_{FE}

●External dimensions (Units : mm)



●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	120	-	-	V	$I_C = 50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	120	-	-	V	$I_C = 1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	-	-	V	$I_E = 50\mu A$
Collector cutoff current	I_{CBO}	-	-	1	μA	$V_{CB} = 100V$
Emitter cutoff current	I_{EBO}	-	-	1	μA	$V_{EB} = 4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	0.4	V	$I_C/I_B = 1A/0.1A$
DC current transfer ratio	h_{FE}	2SC4132, 2SD1857	82	390	-	$V_{CE}/I_C = 5V/0.1A$
		2SD2343	82	270	-	
Transition frequency	f_T	-	80	-	MHz	$V_{CE} = 5V, I_E = -0.1A, f = 30MHz$
Output capacitance	C_{ob}	-	20	-	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$

* Measured using pulse current.